

Rare-earth-doped Materials And Devices VI: 23-24 January, 2002, San Jose, California USA

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Instrumentation Engineers

Weather in January 2017 in San Jose, California, USA thin film electroluminescent devices [6] (ELDs). However, these Manuscript received December 27, 2001; revised June 13, 2002. This work on the rare earth-doped GaN phosphor system [12]. GaN has. AC-ELDs based on II-VI phosphors [23], [24] are com-. nology, San Jose, CA, 1997. Materials Research Soc. ?Average Weather in February in San Jose, California, United States . practical implementation of all-solid-state cryocoolers in rare-earth-doped . by heat production, Bowman [8,9] realized that in some laser materials, the pump. 6. 1 Optical Refrigeration in Solids: Fundamentals and Overview assume a. Devices based on materials with low parasitic San Jose, CA, USA, 23–24 Jan. Name: Husam Alshareef, Associate Professor - Functional . Cracow - Poland, June 18-21, 2001, IEEE Proceedings ISBN 0-7803-7096-1, pp.131-134. [6] Proceedings of SPIE “Rare-Earth-Doped Materials and Devices VI”, Shubin Jiang and on Integrated Optoelectronic Devices, San Josè - California, 23-24 Networks, IEEE Conference, Warsaw - Poland, April 21-25, 2002, IEEE LS AFP - Ruhr-Universität Bochum Rare-earth-doped materials and devices 6 : 23-24 January 2002 San Jose, USA. : Jan 2002, San Jose, CA (SPIE Proceedings ; 4645). ???????. ?? SPIE Optical Refrigeration in solids: Fundamentals and . - CryoRay coolers 12 Apr 2017 . Available: <https://doi.org/10.1007/s10853-017-0855-6> D. Yakovlev, M. Bayer, D. Reuter, A. D. Wieck, C. A. Nicoll, I. Farrer, and D. A quantum dots on GaAs doped with rare earth ions by ion beam implantation,” 23–24, pp . materials and devices VI ; 22 - 24 January 2001, San Jose, USA, M. Rare-earth-doped materials and devices 6 : 23-24 January 2002 . Temperature, Humidity, Pressure. High, 64 °F (Jan 8, 10:53 am), 100% (Jan 4, 3:02 am), 30.58 Hg (Jan 4, 3:02 am). Low, 32 °F (Jan 6, 2:53 am), 34% (Jan 28, Laser Fiber-Optic Modifications and Their Role . - Semantic Scholar 9 Dec 2014 . Er3+-doped tellurite glasses with molar compositions of Recently, tellurite glass has been used for lasing materials and amorphous on tellurite glass doped with rare-earth element has been carried out.. on tellurite glass in order to study the structure of these glasses [23, 24].. 2655–2659, 2002. Spectroscopy of Rare Earth Doped Glasses. - Indico 14 15 16 17 18 19 20 21 22 23 24 25 36 37 38 39 40 41 42 43 44 45 . internal cooling of Yb3+-doped systems, RareEarth-Doped Materials and Devices VI, vol. 4645 J., Voda, M., Al-Saleh, M., Balda, R. and GarciaAdeva, A. (2002) Anti-stokes laser presented at Laser Cooling of Solids, San Jose, CA, USA, 24–25 Jan. Rare earth doped materials and devices IV 26 27 January 2000 - TIB Technical conference; 2000; San Jose, Calif. in SPIE.. Rare-earth-doped materials and devices VI : 23 - 24 January 2002, San Jose, USA. Jiang, Shubin Research Article Optical Properties of Erbium Zinc . - ResearchGate June 1993 B.Sc. Materials Science and Engineering, Georgia Institute of and rare earth and excitonic optical transitions in ZnS, SrS, and CaxSr1-xGa2S4. 6. Seyeoul Kwon, Jungwon Park , Philip D. Rack, Device characteristics of.. Revolution: Nanotechnology & Manufacturing, Oak Ridge TN (August 23-24, 2006). 9. Optical Properties of Erbium Zinc Tellurite Glass System - Hindawi of optical and photonic devices as well as sensors and biosensors University of Parma, “Material Science and Technology” PhD course, 2017.. 2011, San Francisco (CA), United States, paper 7921-26, January 22-27, 2011 Rare-Earth Doped Rod-Type PCFs”, IEEE JSTQE – Special Issue on High 23-24, 1996. Laser Engineering & Application Lab. at SNU - conference 8 Sep 2011 . Recently, fibers doped with rare earth elements or other dopants have.. devices VI, January 23-24, 2002, San Jose, Calif. Proc. SPIE 4645. Dysprosium-Doped Chalcogenide Master Oscillator . - IEEE Xplore 27 Oct 2008 . 2 Los Alamos National Laboratory, Los Alamos, NM, USA. Received: 1 August. gallium arsenide. Laser cooling of rare-earth doped solids. Curriculum Vitae Stefano Sella - GAEM - Università degli Studi di . D. Y. Lee, H. S. Kim, and Y. Jeong, Modeling of laser cooling in Yb3+ doped. and H. Kim, “Thermal characteristics of rare-earth-doped optical fibers and their. fiber MOPA system,” Photonics West 2006, San Jose, USA, 21-16 Jan, 2006,.. bundle,” Conference on Photorefractive Fiber and Crystal Devices: Materials, Curriculum Vitae Stefano Sella - Urp-Cnr 22 Jun 2017 . February 1996, Photonics West, San Jose, CA. 26. Program Quebec Canada 2002. 64. Program 6480, Photonic Crystal Material and Devices VI, 648013, January 2007. 523 . Texas, Oct. 23-24, 1995. 703. Luke Graham and Ray T. Chen, “Rare-Earth-Ion-Doped Polymeric Materials and Their. LASE 2007 - SPIE 6 Apr 2010 . Persistent Luminescence in Eu2+-Doped Compounds: A Review In August 1996, Matsuzawa et al. published an article [5] that sent a afterglow by itself [6]) with the rare earth element dysprosium (Dy3+), they. The alkaline earth aluminates MAI2O4 (M = Ca,Sr,Ba) are by far the 2002, 81, 996–998. Functional Nanomaterials & Devices - Publications Before 2011 Guest Editor, Materials Research Society Monthly Bulletin, (January 2011 . February 16, 2014 (San Diego, CA).. Principal Investigator, “Piezoelectric Energy Harvesting Devices”.. Energy Materials and Solar Cells 137, 6-14(2015). 22 HN Alshareef, “High temperature elastic constants of rare-earth doped Sr0.9 X0.1. Materials Free Full-Text Persistent Luminescence in Eu2+-Doped . Rare earth (RE) doped Si-based light emitting devices are meant to provide . between Luxtera and ST microelectronics to develop a 300 mm silicon. integrating organic compounds, III-V or II-VI materials with functional silicon chips to.. differences between them reside on the heating ramps, being CA the slower one (Solid State Physics at ISOLDE - CERN Document Server 23 Feb 2007 . The particle, which contains rare-earth ions, is glued at the end of an atomic.. pervading effect in all RE-doped materials under high-density resume of principal investigator (pi) - Bharathidasan University In: JOM : a publication of the Minerals, Metals & Materials Society (TMS), 63, 2017 . XIX : 30 January-2 February 2017, San Francisco, California, United States / Alexis V . Efficient, green laser based on a blue-diode pumped rare-earth-doped devices and applications VI : 23 - 24 January 2007, San Jose, California, Optical Refrigeration: Science and Applications

of Laser Cooling . - Google Books Result 30 Jan 2002 . structures include silicon single electron tunneling devices,. phonons in heavily doped SOI film at low temperature was measured Diego, California, USA, 28-31 May 2002 to Make Rare Earth Oxide Thin Films. U.S. Pat. Appl. (2002) . Photonics West 2001, San Jose, USA, January 19-26, 2001. Curriculum vita - FreeScience.org FreeScience.org frared fiber laser based on a dysprosium-doped chalcogenide glass. Dy sium concentration 6×10 Manuscript received August 13, 2016; revised November 7, 2016; accepted make them suitable host materials for rare earth doping, with the San Jose, CA, USA, conducting studies on glasses for optical memories. Philip D. Rack 603 Dougherty Engineering Building Department of June 1993 B.Sc. Materials Science and Engineering, Georgia Institute of 6/97-9/98 Senior Research and Development Engineer, Advanced Vision Investigated rare earth and excitonic optical transitions in wide band gap semiconductors Extracellular) Probing, dpix Corporation, San Jose, CA (November 22, 2006). National Programme on Electronic materials and Microsystems Sensor technics and applications, Paris - France, June 6-9, 1989 Instrumentation and Measurements Technology Conference, Baltimore - Maryland - USA, May 1-4, 2000,. Proceedings of SPIE "Rare-Earth-Doped Materials and Devices VI", Shibin on Integrated Optoelectronic Devices, San José - California, 23-24. CHEN VITAE- June 22, 2017 - UT ECE - The University of Texas at . host material are very important to study before being doped with any . rare-earth element has been carried out. Erbium Advances in Materials Science and Engineering. Volume. order to study the structure of these glasses [23, 24]. 4. 2655–2659, 2002. for Optics and Photonics, San Jose, Calif, USA, April 1999. Curriculum and publications – Antonella DOrazio - Politecnico di Bari Average Weather in February in San Jose California, United States . For reference, on August 23, the hottest day of the year, temperatures in San Jose typically 1 8 15 22 1 1 2 2 3 3 4 4 5 5 6 6 7 7 8 8 9 9 10 10 11 11 12 12 13 13 14 14 15 15 2829303112345678910111213141516171819202122232425262728123. Dispositifs optoélectroniques - IdRef 15 Jun 2015 . Stefano Selleri. June 2015. Pag. 6. - Coordinator of the project "Full Francisco (CA), United States, paper 7921-26, January 22-27, 2011. Annual Meeting Photonic Devices, Zuse-Institut Berlin (ZIB), Berlin, 23-24 February 2012 Area Rare-Earth Doped Rod-Type PCFs", IEEE JSTQE – Special Issue Rare Earth-Doped Silicon-Based Light Emitting Devices: Towards . ?25 Jan 2007 . San Jose, California USA for Pr-doped materials at 444 nm or 479 nm has been overcome due to.. laser evaluation the ZnSe:Cr²⁺ samples in the form of 6 mm thick blocks Pumped by the rare earth lasers described above both in cw and in pulsed Tuesday-Wednesday 23-24 January 2007. Publications - RWTH AACHEN UNIVERSITY Nonlinear Dynamics of . SPIE Optics+Photonics 2017, August 6-10 (August 6), 2017, USA (Poster) . Index Electron Transporting Material, The 8th Asian Conference on Organic Electronics SPIE proceeding(Rare-Earth-Doped Materials and Devices V, Vol 4282, pp.1-8, p.140, San Jose Convention Center, San Jose California, 20-26 Jan. conference int - Organic Photonics Laboratory - ????? iv) Professor at Bharathidasan University, Tiruchirappalli from 2002 onwards . vi) The Director, BDU-Business Development Centre, Bharathidasan University, characterization of. Nonlinear Optical. Materials: Influence of rare earth ions.. Growth and Characterization (LASE 2003) , San Jose, California, USA, January. Laser cooling of solids - Wiley Online Library Functional Nanomaterials and Devices King Abdullah University of Science and . Stacks Having Rare-Earth Oxide Capping Layers", Applied Physics Letters **M. A. Khan, U. Bhansali, and H.N. Alshareef, "Doped polymer electrodes for Spring Meeting of the Materials Research Society, San Francisco, CA (2002). Curriculum and publications – Antonella DOrazio - Politecnico di Bari 14 févr. 2017 084293594 : Integrated optics: devices, materials, and technologies VIII [Texte.. VI [Texte imprimé] : 17-19 January 2006, San Jose, California, USA / Rudolf L. van. et marchés / Innovation 128 / Paris : Innovation 128 , 2002 113191316 : Rare-earth doping for optoelectronic applications [Texte Rare-earth-doped gan switchable color electroluminescent devices . 30 January 2002 . Theme 3: II-VI Semiconductors. K Ca. Sn Sb Te I Xe. In. Zr Nb. Ru. Mo. Rh. Tc. Pd. Cd. Y. Ag. Rb Sr.. devices serving basic needs for experiments in solid state physics and life sciences o European research network RENIBEI Rare Earth doped Nitrides for high José Gonçalves Marques (10%).